

**WEST**

Generate Collection

Print

L2: Entry 23 of 36

File: JPAB

Sep 2, 1994

PUB-NO: JP406244286A

DOCUMENT-IDENTIFIER: JP 06244286 A

TITLE: MANUFACTURE OF SEMICONDUCTOR DEVICE

PUBN-DATE: September 2, 1994

## INVENTOR-INFORMATION:

NAME

COUNTRY

WATANABE, TOKUJIRO

## ASSIGNEE-INFORMATION:

NAME

COUNTRY

NEC CORP

APPL-NO: JP05024617

APPL-DATE: February 15, 1993

US-CL-CURRENT: 438/624; 438/FOR.355

INT-CL (IPC): H01L 21/90; H01L 21/312; H01L 21/318

## ABSTRACT:

PURPOSE: To improve a semiconductor device provided with multilayered wirings in reliability protecting an upper wiring against disconnection caused by steps and constriction by a method wherein an interlayer insulating film is enhanced in evenness.

CONSTITUTION: A silicone polyimide resin film 5 and a photoresist film 9 are successively laminated on a silicon nitride film 4 provided onto the surface of a lower wiring 3 to make the upside flat, the photoresist film 9 and the silicon polyimide resin film 5 arc successively etched back to make the surface of the silicon nitride film 4 exposed, and the silicon polyimide resin film 5 is embedded flat between the lower wirings 3. A silicon oxide film 6 is deposited thereon for the formation of an interlayer insulating film whose upside is flat, whereby a second upper wiring 7 is enhanced in step coverage and protected against disconnection caused by steps and constriction.

COPYRIGHT: (C)1994, JPO&amp;Japio